

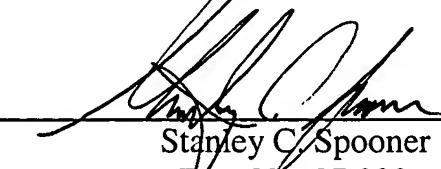
REMARKS

Attached hereto is a marked-up version of the changes made to the specification and claim(s) by the current amendment. The attached page(s) is captioned "Version With Markings To Show Changes Made."

Respectfully submitted,

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**VERSION WITH MARKINGS TO SHOW CHANGES MADE
IN THE CLAIMS**

4. (*Amended*) A semiconductor active backplane according to [any preceding] claim 1 wherein there is a single active element at each location of the array proved by a single transistor.

5. (*Amended*) A semiconductor active backplane according to [any preceding] claim 1 wherein the active element(s) have a MOS construction.

6. (*Amended*) A semiconductor active backplane according to [any preceding] claim 1 wherein substantially the whole of each active element is covered by a metallic conductor, or a pair of metallic conductors.

9. (*Amended*) A backplane according to [any preceding] claim 1 wherein the array of active elements is covered by an insulating layer, each said active element being connected to a metal electrode on said insulating layer, the array of said metal electrodes thus formed covering more than 65% of the area of said array.